

Docket No. 248397US99DIV



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN THE APPLICATION OF: Jamal RAMDANI, et al.

SERIAL NO: 10/768,108

FILED: February 2, 2004

GAU: 2815

EXAMINER: BAUMEISTER

SEMICONDUCTOR STRUCTURE, SEMICONDUCTOR DEVICE, COMMUNICATING DEVICE, INTEGRATED CIRCUIT, AND PROCESS FOR FABRICATING THE SAME

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, and copies were submitted in Application Serial No. 09/808,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

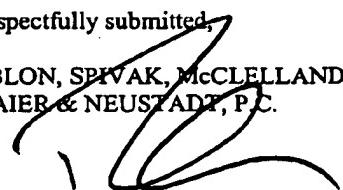
CERTIFICATION

- Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

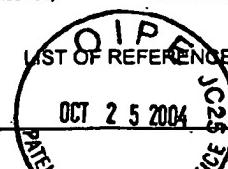
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Form PTO 1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  OCT 25 2004 JC25		ATTY DOCKET NO. 248397US99DIV		SERIAL NO. 10/768,108	
		APPLICANT		Jamal RAMDANI, et al.	
		FILING DATE		February 2, 2004	
				GROUP	
U.S. PATENT DOCUMENTS					
EXAMINER INITIAL	TRADEMARK OFFICE	DOCUMENT NUMBER	DATE	NAME	CLASS
					SUB CLASS
AA		3,802,967	04/09/74	Ladany et al.	
AB		4,174,422	11/13/79	Matthews et al.	
AC		4,404,265	09/13/83	Manasevit	
AD		4,482,906	11/13/84	Hovel et al.	
AE		4,523,211	06/11/85	Morimoto et al.	
AF		4,661,176	04/28/87	Manasevit	
AG		4,793,872	12/27/88	Meunier et al.	
AH		4,846,926	07/11/89	Kay et al.	
AJ		4,855,249	08/08/89	Akasaki et al.	
AI		4,891,091	01/02/90	Shastry	
AK		4,912,087	03/27/90	Aslam et al.	
AL		4,928,154	05/22/90	Umeno et al.	
AM		4,963,949	10/16/90	Wanlass et al.	
AN		5,141,894	08/25/92	Bisaro et al.	
AO		5,159,413	10/27/92	Calviello et al.	
AP		5,173,474	12/22/92	Connell et al.	
AQ		5,221,367	06/22/93	Chisholm et al.	
AR		5,225,031	07/06/93	McKee et al.	
AS		5,358,925	10/25/94	Neville Connell et al.	
AT		5,393,352	02/28/95	Summerfelt	
AU		5,418,216	05/23/95	Fork	
AV		5,450,812	09/19/95	McKee et al.	
AW		5,478,653	12/26/95	Guenzer	
AX		5,482,003	01/09/96	McKee et al.	
AY		5,514,484	05/07/96	Nashimoto	
AZ		5,556,463	09/17/96	Guenzer	
BA		5,588,995	12/31/96	Sheldon	
BB		5,670,798	09/23/97	Schetzina	
BC		5,733,641	03/31/98	Fork et al.	
BD		5,735,949	04/07/98	Manti et al.	
BE		5,741,724	04/21/98	Ramdani et al.	
BF		5,810,923	09/22/98	Yano et al.	
BG		5,830,270	11/03/98	McKee et al.	
BH		5,912,068	06/15/99	Jia	
BI		6,020,222	02/01/00	Wollesen	
BJ		6,045,626	04/04/00	Yano et al.	
BK		6,064,078	05/16/00	Northrup et al.	
BL		6,064,092	05/16/00	Park	
BM		6,096,584	08/01/00	Ellis-Monaghan et al.	
BN		6,103,008	08/15/00	McKee et al.	
BO		6,136,666	10/24/00	So	
BP		6,174,755	01/16/01	Manning	
BQ		6,180,486	01/30/01	Leobandung et al.	

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LIST OF REFERENCES CITED BY APPLICANT			APPLICANT Jamal RAMDANI, et al.				
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
CA		3,766,370	10/16/73	Walther			
CB		4,006,989	02/08/77	Andringa			
CC		4,284,329	08/18/81	Smith et al.			
CD		4,777,613	10/11/98	Shahan et al.			
CE		4,802,182	01/31/89	Thomton et al.			
CF		4,882,300	11/21/89	Inoue et al.			
CG		4,896,194	01/23/90	Suzuki			
CH		4,999,842	03/12/91	Huang et al.			
CI		5,081,062	01/14/92	Vasudev et al.			
CJ		5,155,658	10/13/92	Inam et al.			
CK		5,248,564	09/28/93	Ramesh			
CL		5,260,394	11/09/93	Tazaki et al.			
CM		5,270,298	12/14/93	Ramesh			
CN		5,286,985	02/15/94	Taddiken			
CO		5,310,707	05/10/94	Oishi et al.			
CP		5,326,721	07/05/94	Summerfelt			
CQ		5,404,581	04/04/95	Honjo			
CR		5,418,389	05/23/95	Watanabe			
CS		5,436,759	07/25/95	Dijaili et al.			
CT		5,576,879	11/19/96	Nashimoto			
CU		5,606,184	02/25/97	Abrokwah, et al.			
CV		5,640,267	06/17/97	May et al.			
CW		5,674,366	10/07/97	Hayashi et al.			
CX		5,729,641	03/17/98	Chandonnet et al.			
CY		5,790,583	08/04/98	Ho			
CZ		5,825,799	10/20/98	Ho et al.			
DA		5,857,049	01/05/99	Beranek et al.			
DB		5,874,860	02/23/99	Brunel et al.			
DC		5,926,496	07/20/99	Ho et al.			
DD		5,937,285	08/10/99	Abrokwah, et al.			
DE		5,981,400	11/09/99	Lo			
DF		5,990,495	11/23/99	Ohba			
DG		6,002,375	12/14/99	Corman et al.			
DH		6,008,762	12/28/99	Nghiem			
DI		6,055,179	04/25/00	Koganei et al.			
DJ		6,107,653	08/22/00	Fitzgerald			
DK		6,113,690	09/05/00	Yu et al.			
DL		6,114,996	09/05/00	Nghiem			
DM		6,121,642	09/19/00	Newns			
DN		6,128,178	10/03/00	Newns			
DO		6,143,072	11/07/00	McKee et al.			
DP		6,184,144	02/06/01	Lo			
DQ		6,222,654	04/24/01	Frigo			

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<b>U.S. PATENT DOCUMENTS</b>						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
EA	4,484,332	11/20/84	Hawrylo			
EB	4,815,084	03/21/89	Scifres et al.			
EC	4,876,219	10/24/89	Eshita et al.			
ED	4,963,508	10/16/90	Umeno et al.			
EE	5,060,031	10/22/91	Abrokwah, et al.			
EF	5,063,166	11/05/91	Mooney et al.			
EG	5,116,461	05/26/92	Lebby et al.			
EH	5,127,067	06/30/92	Delcoco et al.			
EI	5,144,409	09/01/92	Ma			
EJ	5,293,050	03/08/94	Chappie-Sokol et al			
EK	5,356,831	10/18/94	Calviello et al.			
EL	5,391,515	02/21/95	Kao et al.			
EM	5,442,191	08/15/95	Ma			
EN	5,444,016	08/22/95	Abrokwah, et al.			
EO	5,480,829	01/02/96	Abrokwah, et al.			
EP	5,528,414	06/18/96	Oakley			
EQ	5,614,739	03/25/97	Abrokwah et al.			
ER	5,729,394	03/17/98	Sevier et al.			
ES	5,731,220	03/24/98	Tsu et al.			
ET	5,764,676	06/09/98	Paoli et al.			
EU	5,777,762	07/07/98	Yamamoto			
EV	5,778,018	07/07/98	Yoshikawa et al.			
EW	5,778,116	07/07/98	Tomich			
EX	5,801,105	09/01/98	Yano et al.			
EY	5,828,080	10/27/98	Yano et al.			
EZ	5,858,814	01/12/99	Goossen et al.			
FA	5,861,966	01/19/99	Ortel			
FB	5,883,996	03/16/99	Knapp et al.			
FC	5,995,359	11/30/99	Klee et al.			
FD	6,058,131	05/02/00	Pan			
FE	6,137,603	10/24/00	Henml			
FF	6,146,906	11/14/00	Inoue et al.			
FG	6,173,474	01/16/01	Conrad			
FH	6,180,252	01/30/01	Farrell et al.			
FI	4,242,595	12/30/0	Lehovec			
FJ	4,398,342	08/16/83	Pitt et al.			
FK	4,424,589	01/03/84	Thomas et al.			
FL	4,876,208	10/24/89	Gustafson et al.			
FM	4,482,422	11/84	McGinn et al.			
FN	4,667,088	05/19/87	Kramer			
FO	4,772,929	09/20/88	Manchester et al.			
FP	4,841,775	06/27/89	Ikeda et al.			
FQ	4,845,044	07/04/89	Ariyoshi et al.			

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
GA		4,868,376	09/19/89	Lessin et al.			
GB		4,885,376	12/05/89	Verkade			
GC		4,888,202	12/89	Murakami et al.			
GD		4,891,091	12/90	Wanlass et al.			
GE		5,051,790	09/24/91	Hammer			
GF		5,055,445	10/08/91	Belt et al.			
GG		5,081,519	11/14/92	Nishimura et al.			
GH		5,143,854	09/01/92	Pirnung et al.			
GI		5,185,589	02/09/93	Krishnaswamy et al.			
GJ		5,191,625	03/02/93	Gustavsson			
GK		5,194,397	03/16/93	Cook et al.			
GL		5,208,182	05/04/93	Narayan et al.			
GM		5,216,729	06/01/93	Berger et al.			
GN		5,314,547	05/24/94	Heremans et al.			
GO		5,352,926	10/04/94	Andrews			
GP		5,356,509	10/18/94	Terranova et al.			
GQ		5,371,734	12/06/94	Fischer			
GR		5,372,992	12/94	Itozaki et al.			
GS		5,405,802	04/11/95	Yamagata et al.			
GT		5,442,561	08/15/95	Yoshizawa et al.			
GU		5,453,727	09/26/95	Shibasaki et al.			
GV		5,466,631	11/14/95	Ichikawa et al.			
GW		5,473,047	12/05/95	Shi			
GX		5,473,171	12/95	Summerfelt			
GY		5,479,033	12/26/95	Baca et al.			
GZ		5,486,406	01/23/96	Shi			
HA		5,491,461	02/13/96	Partin et al.			
HB		5,492,859	02/20/96	Sakaguchi et al.			
HC		5,494,711	02/27/96	Takeda et al.			
HD		5,504,035	04/02/96	Rostoker et al.			
HE		5,504,183	04/02/96	Shi			
HF		5,511,238	04/23/96	Bayraktaroglu			
HG		5,512,773	04/96	Wolf et al.			
HH		5,515,047	05/07/96	Yamakido et al.			
HI		5,515,810	05/14/96	Yamashita et al.			
HJ		5,519,235	05/96	Ramesh			
HK		5,549,977	08/96	Jin et al.			
HL		5,551,238	09/03/96	Prueitt			
HM		5,552,547	09/03/96	Shi			
HN		5,589,284	12/31/96	Summerfelt et al.			
HO		5,602,418	02/11/97	Imai et al.			
HP		5,633,724	05/27/97	King et al.			

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY DOCKET NO. 248397US99DIV	SERIAL NO. 10/768,108			
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<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
JA		5,650,646	07/22/97	Summerfelt			
JB		5,656,382	08/12/97	Nashimoto			
JC		5,659,180	08/19/97	Shen et al.			
ID		5,661,112	08/26/97	Hatta et al.			
IE		5,679,965	11/95	Schetzina			
IF		5,725,641	03/10/98	MacLeod			
IG		5,745,631	04/28/98	Reinker			
IH		5,776,621	07/07/98	Nashimoto			
II		5,777,350	07/07/98	Nakamura et al.			
IJ		5,789,845	08/04/98	Wadaka et al.			
IK		5,792,569	08/11/98	Sun et al.			
IL		5,792,679	08/11/98	Nakato			
IM		5,796,648	08/18/98	Kawakubo et al.			
IN		5,801,072	09/01/98	Barber			
IO		5,812,272	09/22/98	King et al.			
IP		5,814,583	09/98	Itozaki et al.			
IQ		5,825,055	10/20/98	Summerfelt			
IR		5,827,755	10/27/98	Yonchara et al.			
IS		5,833,603	11/10/98	Kovacs et al.			
IT		5,838,035	11/17/98	Ramesh			
IU		5,844,260	12/01/98	Ohori			
IV		5,846,846	12/08/98	Suh et al.			
IW		5,863,326	01/26/99	Nause et al.			
IX		5,872,493	02/16/99	Ella			
IY		5,879,956	03/99	Seon et al.			
IZ		5,880,452	03/09/99	Plesko			
JA		5,883,564	03/16/99	Partin			
JB		5,907,792	05/25/99	Droopad et al.			
JC		5,937,274	08/10/99	Kondow et al.			
JD		5,948,161	09/07/99	Kizuki			
JE		5,959,879	09/28/99	Koo			
JF		5,966,323	10/99	Chen et al.			
JG		5,987,011	11/16/99	Toh			
JH		6,022,140	02/08/00	Fraden et al.			
JI		6,022,410	02/08/00	Yu et al.			
JJ		6,023,082	02/08/00	McKee et al.			
JK		6,028,853	02/22/00	Haartsen			
JL		6,049,702	04/11/00	Tham et al.			
JM		6,078,717	06/20/00	Nashimoto et al			
JN		6,088,216	07/00	Laibowitz et al.			
JO		6,090,659	07/00	Laibowitz et al.			
JP		6,107,721	08/22/00	Lakin			
JQ		6,153,010	11/28/00	Kiyoku et al			

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U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
KA	6,153,454	11/28/00	Krivokapic			
KB	6,191,011	02/01	Gliboa et al			
KC	6,204,737	03/20/01	Ella			
KD	6,224,669	05/01/01	Yi et al.			
KE	6,225,051	05/01/01	Sugiyama et al.			
KF	6,241,821	06/05/01	Yu et al.			
KG	6,265,749	07/24/01	Gardner et al.			
KH	6,313,486	11/01	Kencke et al.			
KI	6,316,832	11/13/01	Tsuzuki et al.			
KJ	2002/0008234	01/02	Emrick			
KK	3,670,213	06/13/72	Nakawaga et al.			
KL	4,756,007	07/05/88	Qureshi et al.			
KM	4,773,063	09/20/88	Hunsperger et al.			
KN	5,394,489	02/28/95	Koch			
KO	5,406,202	04/11/95	Mehrgardt et al.			
KP	5,528,067	06/18/96	Farb et al.			
KQ	5,572,052	11/05/96	Kashihara et al.			
KR	5,767,543	06/16/98	Ooms et al.			
KS	6,175,497	01/16/01	Tseng et al.			
KT	6,197,503	03/06/01	Vo-Dinh et al.			
KU	6,248,459	06/19/01	Wang et al.			
KV	6,252,261	06/26/01	Usui et al.			
KW	6,255,198	07/03/01	Linthicum et al.			
KX	6,268,269	07/31/01	Lee et al.			
KY	6,291,319	09/18/01	Yu et al.			
KZ	6,316,785	11/13/01	Nunoue et al.			
LA	6,343,171	01/29/02	Yoshimura et al.			
LB	4,965,649	10/23/90	Zanio et al.			
LC	6,253,649	05/01	Kawahara et al.			
LD	6,211,096	04/01	Aliman et al.			
LE	6,239,449	05/29/01	Fafard et al.			
LF	2001/0013313	08/16/01	Droopad et al.			
LG	6,184,044	02/06/01	Sone et al.			
LH	6,011,646	01/04/00	Mirkarimi et al.			
LI	5,227,196	07/13/93	Itoh			
LJ	6,150,239	11/21/00	Goesele et al.			
LK	5,441,577	08/15/95	Sasaki et al.			
LL	4,459,325	07/10/84	Nozawa et al.			
LM	4,392,297	07/12/83	Little			
LN	4,289,920	09/15/81	Hovel			
LO	5,281,834	01/25/94	Cambou et al.			
LP	4,901,133	02/13/90	Curran et al.			
LQ	5,514,904	05/07/96	Onga et al.			

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	MA	5,553,089	09/03/96	Seki et al.			
	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
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	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
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	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
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	NE	5,873,977	02/23/99	Desu et al.			
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	NJ	5,280,013	01/18/94	Newman et al.			
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	NO	5,963,291	10/05/99	Wu et al.			
	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	King et al.			

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	OB 4,681,982	07/21/87	Yoshida		
	OC 4,629,821	12/16/86	Bronstein-Bonte et al.		
	OD 4,452,720	06/05/84	Harada et al.		
	OE 3,935,031	01/27/76	Adler		
	OF 5,760,426	06/02/98	Marx et al.		
	OG 5,053,835	10/01/91	Horikawa et al.		
	OH 6,326,645 B1	12/04/01	Kadota		
	OI 5,770,887	06/23/98	Tadatomo et al.		
	OJ 6,372,356 B1	04/16/02	Thornton et al.		
	OK 4,774,205	09/27/88	Choi et al.		
	OL 6,359,330 B1	03/19/02	Goudard		
	OM 5,312,765	05/17/94	Kanber		
	ON 5,734,672	03/31/98	McMinn et al.		
	OO 6,367,699 B2	04/09/02	Ackley		
	OP 5,530,235	06/25/96	Stefik et al.		
	OQ 5,623,552	04/22/97	Lane		
	OR 5,481,102	01/02/96	Hazelrigg, Jr.		
	OS 6,134,114	10/17/00	Ungermann et al.		
	OT 5,984,190	11/16/99	Nevill		
	OU 5,789,733	08/04/98	Jachimowicz et al.		
	OV 5,753,300	05/19/98	Wessels et al.		
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	OX 5,886,867	03/23/99	Chivukula et al.		
	OY 5,028,976	07/02/91	Ozaki et al.		
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	PA 5,596,214	01/21/97	Endo		
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	PN 5,888,296	03/30/99	Ooms et al.		
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	QA	5,776,359	07/07/98	Schultz et al.			
	QB	5,569,953	10/29/96	Kikkawa et al.			
	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wemberg et al.			
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	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
	QP	5,484,664	01/16/96	Kitahara et al.			
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	UB	5,427,988	06/27/95	Sengupta et al.	
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	UR	6,194,753 B1	02/27/01	Seon et al.	
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	UT				
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AAA	0 250 171	12/23/87	EP		X
AAB	0 342 937	11/23/89	EP		X
AAC	0 455 526	06/11/91	EP		X
AAD	0 602 568	06/22/94	EP		X
AAE	0 607 435	07/27/94	EP		X
AAF	1 001 468	05/17/00	EP		X
AAG	0 514 018	11/19/92	EP		X
AAH	0 999 600	05/10/00	EP		X
AAI	1 319 311	06/04/70	Great Britain		X
AAJ	5-291299	11/05/93	Japan w/English Abstract		X
AAK	11-238683	08/31/99	Japan		X
AAL	11-260835	09/24/99	Japan w/English Abstract		X
AAM	HEI 2-391	01/05/90	Japan w/English Abstract		X
AAN	5-48072	02/26/93	Japan w/English Abstract		X
AAO	52-88354	07/23/77	Japan w/English Abstract		X
AAP	54-134554	10/19/79	Japan w/English Abstract		X
AAQ	55-87424	07/02/80	Japan w/English Abstract		X
AAR	61-108187	05/26/86	Japan w/English Abstract		X
AAS	6-232126	08/19/94	Japan		X
AAT	6-291299	10/18/94	Japan w/English Abstract		X
AAU	63-34994	02/15/88	Japan w/English Abstract		X
AAV	63-131104	06/03/88	Japan w/English Abstract		X
AAW	63-198365	08/17/88	Japan w/English Abstract		X
AAX	10-321943	12/04/98	Japan		X
AAY	6-334168	12/02/94	Japan		X
AAZ	WO 99/63580	12/09/99	WIPO		X
ABA	WO 99/14804	03/25/99	WIPO		X
ABB	WO 97/45827	12/04/97	WIPO		
ABC	WO 99/19546	04/22/99	WIPO		
ABD	WO 00/33363	06/08/00	WIPO		
ABE	WO 00/48239	08/17/00	WIPO		
ABF	WO 99/14797	03/25/99	WIPO		
ABG	GB 2 335 792	09/29/99	Great Britain		
ABH	1 109 212	06/20/01	Europe		
ABI	DE 197 12 496	10/30/97	Germany		X
ABJ	60-212018	10/24/85	Japan w/English Abstract		
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ABL	WO 92/10875	06/25/92	WIPO		
ABM	0 682 266	11/15/95	Europe		
ABN	3-41783	02/91	Japan (English Abstract only)		
ABO	0 581 239	02/02/94	Europe		
ABP	0812494	01/16/96	Japan		
ABQ	2 000 1645	06/16/00	Japan		

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BAA	1 043 426	10/11/00	Europe		
BAB	2000-068466	03/00	Japan (Abstract)		
BAC	64-50575	02/27/89	Japan		
BAD	WO 98/05807	01/12/98	WIPO		
BAE	WO 94/03908	02/17/94	WIPO		
BAF	WO 01/33585	05/10/01	WIPO		
BAG	1-102435	04/20/89	Japan w/English Abstract		
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BAI	02051220	02/21/90	Japan (English Abstract)		
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BAK	64-52329	02/28/89	Japan (w/English Abstract)		
BAL	10-256154	09/25/98	Japan (w/English Abstract)		
BAM	DE 196 07 107	08/28/97	Germany	xx	
BAN	10-303396	11/13/98	Japan (w/English Abstract)		
BAO	58-213412	12/12/83	Japan w/English Abstract		
BAP	0 964 259	12/15/99	Europe		
BAQ	0 875 922	11/04/98	Europe		
BAR	61-63015	04/01/86	Japan w/English Abstract		
BAS	11340542	12/10/99	Japan (English Abstract)		
BAT	WO 01/37330	05/25/01	WIPO		
BAU	0 331 467	09/06/89	Europe		
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BAW	0 926 739	06/30/99	Europe		
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BAY	5-152529	06/18/93	Japan w/English Abstract		
BAZ	9-67193	03/11/97	Japan w/English Abstract		
BBA	9-82913	03/28/97	Japan w/English Abstract		
BBB	0 309 270	03/29/89	Europe		
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BBD	EP 0 810 666	12/03/97	Europe		
BBE	1-179411	07/17/89	Japan w/English Abstract		
BBF	DE 100 17 137	10/26/00	GERMANY		
BBG	WO 02 01648	01/03/02	WIPO		
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BBJ	WO 02/09160 A2	01/31/02	WIPO		
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BBL	0 483 993	05/06/92	Europe		
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CAB	EP 1 069 606	01/17/01	Europe	
CAC	WO 02/03113	01/10/02	WIPO	
CAD	WO 02/03467	01/10/02	WIPO	
CAE	0 630 057	12/21/94	EUROPE	
CAF	61-36981	02/21/86	Japan w/English Abstract	
CAG	WO 93/07647	04/15/93	WIPO	
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CAO	JP 58-075868	05/07/83	Japan w/English Abstract	
CAP	EP 0 993 027	04/12/00	Europe	
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CAR	WO 98/20606	05/14/98	WIPO	
CAS	EP 1 043 765	10/11/00	Europe	
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CAV	WO 01/16395	03/08/01	WIPO	
CAW	2000-351692	12/19/00	Japan w/English Abstract	
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CCAB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B41</i> , (1996), pp. 166-173.				
CCAC	W. F. Egelhoff et al., "Optimizing GMR Spin Valves: The Outlook for Improved Properties", <i>1998 Int'l Non Volatile Memory Technology Conference</i> , pp. 34-37.				
CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col, and Motorola Labs, May 11, 2000.				
CCAE	M. Rotter et al., "Nonlinear Acoustoelectric Interactions in GaAs/LiNbO <sub>3</sub> Structures", <i>Applied Physics Letters</i> , Vol. 75(7), August 16, 1999, pp. 965-967.				
CCAF	K. Sreenivas et al., "Surface Acoustic Wave Propagation on Lead Zirconate Titanate Thin Films," <i>Appl. Phys. Lett.</i> 52 (9), Feb. 29, 1998, pp. 709-711.				
CCAG	M. Rotter et al., "Single Chip Fused Hybrids for Acousto-Electric and Acousto-Optic Applications," <i>1997 Applied Physics Letters</i> , Vol. 70(16), April 21, 1997, pp. 2097-2099.				
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CCAI	S. Mathews et al., "Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", <i>Science</i> , Vol. 276, April 11, 1997, pp. 238-240.				
CCAJ	R. Houdre et al., "Properties of GaAs on Si Grown by Molecular Beam Epitaxy," <i>Solid State and Materials Sciences</i> , Vol. 16, Issue 2, 1990, pp. 91-114.				
CCAK	S. F. Fang et al., "Gallium Arsenide and Other Compound Semiconductors on Silicon," <i>J. Appl. Phys.</i> , 68(7), October 1, 1990, pp. R31-R58.				
CCAL	Carlin et al., "Impact of GaAs Buffer Thickness on Electronic Quality of GaAs Grown on Graded Ge/GeSi/Si Substrates, <i>Appl. Phys. Letter</i> , Vol. 76, No. 14, April 2000, pp. 1884-1886.				
CCAM	Ringel et al., "Epitaxial Integration of III-V Materials and Devices with Si Using Graded GeSi Buffers," <i>27<sup>th</sup> International Symposium on Compound Semiconductors</i> , Oct. 2000.				
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CCAQ	Gunapala et al., "Bound-To-Quasi-Bound Quantum-Well Infrared Photodetectors," <i>NASA Tech Brief</i> , Vol. 22, No. 9, September 1998.				
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DDAB	Bruley et al., "Nanostructure and Chemistry of a (100)MgO/(100) GaAs Interface," <i>Appl. Phys Lett.</i> , 65(5), Aug. 1994, pp. 564-566.			
DDAC	Fork et al., "Epitaxial MgO On Si(001) for Y-Ba-Cu-O Thin Film Growth by Pulsed Laser Deposition," <i>Appl. Phys Lett.</i> , 58(20), May 20, 1991, pp. 2294-2296.			
DDAD	Himpsel et al., "Dielectrics on Semiconductors," <i>Materials Science and Engineering</i> , B1(1988), pp. 9-13.			
DDAE	Li et al., "Epitaxial La <sub>0.67</sub> Sr <sub>0.33</sub> MnO <sub>3</sub> Magnetic Tunnel Junctions," <i>J. Appl. Phys.</i> 81(8), Apr. 15, 1997, pp. 5509-5511.			
DDAF	O'Donnell et al., "Colossal Magnetoresistance Magnetic Tunnel Junctions Grown by Molecular-Beam Epitaxy," <i>Appl. Physics Letters</i> , Vol. 76, No. 14, April 3, 2000, pp. 1914-1916.			
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DDAH	T. Asano et al., "An Epitaxial Si/Insulator/Si Structure Prepared by Vacuum Deposition of CaF <sub>2</sub> and Silicon," <i>Thin Solid Films</i> , Vol. 93 (1982), pp. 143-150.			
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DDAL	"Technical Analysis of Qualcomm QCP-800 Portable Cellular Phone (Transmitter Circuitry)," Talus Corporation, Qualcomm QCP-800 Technical Analysis Report, December 10, 1996, pp. 5-8.			
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DDAQ	Kihong KIM, et al." On-Chip Wireless Interconnection with Integrated Antennas"; 2000 IEEE; pp. 20.2.1-20.3.4			
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EEAP	D.E. ASPNES, et al.; "Steps on (001) silicon surfaces"; <i>J. Vac. Sci. Technol. B</i> , Vol. 5, No. 4, Jul/Aug 1987; pp. 939-944		
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FFAO	Ronald W. WAYNANT, et al.; "OPTOELECTRONIC INTEGRATED CIRCUITS"; ELECTRO-OPTICS HANDBOOK, McGraw-Hill, Inc., 1994; Chapter Twenty Seven			
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	GGAB	Peter S. GUILFOYLE, et al.: "Optoelectronic Architecture for High-Speed Switching and Processing Applications"; 1998 The Photonics Design and Applications Handbook; pp. H-399-H-406	
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IIAP	M. Schreiter, et al.; "Sputtering of Self-Polarized PZT Films for IR-Detector Arrays"; 1998 IEEE; pp. 181-185		
IIAQ	Hideaki Adachi et al.; "Sputtering Preparation of Ferroelectric PLZT Thin Films and Their Optical Applications"; IEEE Transactions of Ultrasonics, Ferroelectrics and Frequency Control, Vol. 38, No. 6, November 1991		
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JJAA	A.J. Moulson et al.; "Electroceramics Materials Properties Applications"; Chapman & Hall; pp. 366-369		
JJAB	P.A. Langjahr et al.; "Epitaxial Growth and Structure of Cubic and Pseudocubic Perovskite Films on Perovskite Substrates"; Mat. Res. Soc. Symp. Proc., Vol. 401; 1995 Materials Research Society; pp. 109-114		
JJAC	Wang et al.; "Depletion-Mode GaAs MOSFETs with Negligible Drain Current Drift and Hysteresis"; Electron Devices Meeting, 1998, IEDM '98 Technical Digest; pp. 67-70		
JJAD	Ben G. Streetman; "Solid State Electronic Devices"; 1990, Prentice Hall; Third Edition; pp. 320-322		
JJAE	A.Y Wu et al.; "Highly Oriented (Pb,La)(Zr,Ti)O <sub>3</sub> Thin Films on Amorphous Substrates"; IEEE, 1992; pp. 301-304		
JJAF	Timothy E. Glassman et al.; "Evidence for Cooperative Oxidation of MoCVD Precursors Used in Ba <sub>x</sub> Sr <sub>1-x</sub> TiO <sub>3</sub> Film Growth"; Mat. Res. Soc. Symp. Proc. Vol. 446, 1997 Materials Research Society; pp. 321-326		
JJAG	S.N. Subbarao et al.; "Monolithic PIN Photodetector and FET Amplifier on GaAs-on-Si"; IEEE; GaAs IC Symposium-163-166; 1989		
JJAH	T.A. Langdo et al.; "High Quality Ge on Si by Epitaxial Necking"; Applied Physics Letters; Vol. 76, No. 25; pp. 3700-3702; June 19, 2000		
JJAI	Chenning Hu et al.; Solar Cells From Basics to Advanced Systems; McGraw-Hill Book Company; 1983		
JJAJ	O.J. Painter et al; "Room Temperature Photonic Crystal Defect Lasers at Near-Infrared Wavelengths in InGaAsP"; Journal of Lightwave Technology, Vol. 17, No. 11; November 1999		
JJAK	C. Donn et al.; "A 16-Element, K-Band Monolithic Active Receive Phased Array Antenna"; Antennas and Propagation Society International Symposium, 1988; pp.188-191, Vol. 1; 6-10 June 1988		
JJAL	Don W. Shaw; "Epitaxial GaAs on Si: Progress and Potential Applications"; Mat. Res. Soc. Symp. Proc.; pp.15-30; 1987		
JJAM	G.J.M. Domans, et al.; "PbTiO <sub>3</sub> /Thin Films Grown by Organometallic Chemical Vapour Deposition"; Third International Symposium on Integrated Ferroelectrics; April 3-5, 1991 (Abstract)		
JJAN	P.J. Borrelli et al.; "Compositional and Structural Properties of Sputtered PLZT Thin Films"; Ferroelectric Thin Films II Symposium; Dec. 2-4, 1991 (Abstract)		
JJAO	Ranu Nayak et al; "Enhanced acousto-optic diffraction efficiency in a symmetric SrTiO <sub>3</sub> /BaTiO <sub>3</sub> /SrTiO <sub>3</sub> thin-film heterostructure"; 1 November 2000; Vol. 39, No. 31; Applied Optics; pp. 5847-5853		
JJAP	Ranu Nayak et al; "Studies on acousto-optical interaction in SrTiO <sub>3</sub> /BaTiO <sub>3</sub> /SrTiO <sub>3</sub> epitaxial thin film heterostructures"; J. Phys. D: Appl. Phys. 32 (1999) 380-387		
JJAQ	S.K. Tewksbury et al.; "Cointegration of Optoelectronics and Submicron CMOS"; Wafer Scale Integration; 1993; Proceedings, Fifth Annual IEEE; 20 January 1993; pp. 358-367		
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KKAA	V. Kaushik et al.; "Device Characteristics of Crystalline Epitaxial Oxides on Silicon"; Device Research Conference, 2000; Conference Digest 58th DRC; pp. 17-20; June 19-21, 2000			
KKAB	Katherine Derbyshire; "Prospects Bright for Optoelectronics Volume, Cost Drive Manufacturing for Optical Applications"; Semiconductor Magazine; Vol. 3, No. 3; March 2002			
KKAC	Alex Chediak et al; "Integration of GaAs/Si with Buffer Layers and Its Impact on Device Integration"; TICS 4, Prof. Sands. MSE 225, April 12, 2002; pp. 1-5			
KKAD	S.A. Chambers et al; "Band Discontinuities at Epitaxial SrTiO <sub>3</sub> /Si(001) Heterojunctions"; Applied Physics Letters; Vol. 77, No. 11; September 11, 2000; pp. 1662-1664			
KKAE	H. Wang et al.; "GaAs/GaAlAs Power HBTs for Mobile Communications"; Microwave Symposium Digest; 1993 IEEE; Vol. 2.; pp. 549-552			
KKAF	Y. Ota et al.; "Application of Heterojunction FET to Power Amplifier for Cellular Telephone"; Electronics Letters; 26th May 1994; Vol. 30, No. 11; pp. 908-907			
KKAG	Keiichi Sakuno et al; "A 3.5W HBT MMIC Power Amplifier Module for Mobile Communications"; IEEE 1994; Microwave and Millimeter-Wave Monolithic Circuits Symposium; pp. 63-66			
KKAH	Mitsubishi Semiconductors Press Release (GaAs FET's) November 8, 1999 pp.1-2			
KKAI	R.J. Matyi et al; "Selected Area Heteroepitaxial Growth of GaAs on Silicon for Advanced Device Structures"; 2194 Thin Solid Films; 181 (1989) December 10; No. 1; pp. 213-225			
KKAJ	K. Nashimoto et al; "Patterning of Nb, LaOnZr, TiO <sub>3</sub> Waveguides for Fabricating Micro-Optics Using Wet Etching and Solid-Phase Epitaxy"; Applied Physics Letters; Vol. 75, No. 8; 23 August 1999; pp. 1054-1056			
KKAK	Bang-Hung Tsao et al; "Sputtered Barium Titanate and Barium Strontium Titanate Films for Capacitor Applications"; Applications of Ferroelectrics, 2000; Proceedings of the 2000 12th International Symposium on Vol. 2; pp. 837-840			
KKAL	Man Fal Ng et al; "Heteroepitaxial growth of lanthanum aluminate films derived from mixed metal nitrates"; Journal of Materials Research; Vol. 12, No. 5; pp. 1308			
KKAM	Yuji Matsumoto et al.; "Room-Temperature Ferromagnetism in Transparent Transition Metal-Doped Titanium Dioxide"; Science; 2 February 2001; Vol. 291; pp. 854-856			
KKAN	S.A. Chambers et al.; "Epitaxial Growth and Properties of Ferromagnetic Co-Doped TiO <sub>2</sub> Anatase"; Applied Physics Letters; Vol. 79, No. 21; November 19, 2001; pp. 3467-3469			
KKAO				
KKAP				
KKAQ				
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	UT	5,528,209	06/18/96	Macdonald et al.			
	UV	5,998,781	12/07/99	Vawter et al.			
	UW	6,110,813	08/29/00	Ota et al.			
	UX	6,452,232 B1	09/17/02	Adan			
	UY	6,049,110	04/11/00	Koh			
	UZ	5,559,368	09/24/96	Hu et al.			
	VA	6,392,253 B1	05/21/02	Saxena			
	VB	5,585,288	12/17/96	Davis et al.			
	VC	5,268,327	12/07/93	Vernon			
	VD	6,198,119 B1	03/06/01	Nabatame et al.			
	VE	6,113,225	09/05/00	Miyata et al.			
	VF	5,262,659	11/16/93	Grudkowski et al.			
	VG	6,239,012 B1	05/29/01	Kinsman			
	VH	6,297,598	10/02/01	Wang et al.			
	VI	2002/140012	10/03/02	Droopad			
	VJ	4,866,489	09/12/89	Yokogawa et al.			
	VK	6,080,378	06/27/00	Yokota et al.			
	VL	5,508,554	04/16/96	Takatani et al.			
	VM	6,477,285 B1	11/05/02	Shanley			
	VN	4,695,120	09/22/87	Holder			
	VO	5,882,948	03/16/99	Jewell			
	VP	5,574,589	11/12/96	Feuer et al.			
	VQ	5,510,665	04/23/96	Conley			
	VR	4,804,866	02/14/89	Akiyama			
	VS	5,057,694	10/15/91	Idaka et al.			
	VT	5,635,453	06/03/97	Pique et al.			
	VU	5,719,417	02/17/98	Roeder et al.			
	VV	5,998,819	12/07/99	Yokoyama et al.			
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VW	2002/0079576	06/27/02	Seshan		
VX	5,148,504	09/15/92	Levi et al.		
VY	2002/0195610 A1	12/26/02	Klosowiak		
VZ	5,477,363	12/19/95	Matsuda		
WA	5,905,571	05/18/99	Butler et al.		
WB	5,570,226	10/29/96	Ota		
WC	5,087,829	02/11/92	Ishibashi et al.		
WD	2001/0020278 A1	09/06/01	Saito		
WE	6,496,469 B1	12/17/02	Uchizaki		
WF	5,679,947	10/21/97	Doi et al.		
WG	2001/0036142 A1	11/01/01	Kadowaki et al.		
WH	5,446,719	08/29/95	Yoshida et al.		
WI	5,831,960	11/03/98	Jiang et al.		
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WQ	3,617,951	11/02/71	Anderson		
WR	5,838,053	11/17/98	Bevan et al.		
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WT	5,959,308	09/28/99	Shichijo et al.		
WU	5,362,972	11/08/94	Yazawa et al.		
WV	5,864,171	01/26/99	Yamamoto et al.		
WW	5,028,563	07/02/91	Feit et al.		
WX	5,937,115	08/10/99	Domash		
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	WY	5,878,175	03/02/99	Sonoda et al.			
	WZ	4,801,184	01/31/89	Revelli			
	XA	5,140,387	08/18/92	Okazaki et al.			
	XB	5,410,622	04/25/95	Okada et al.			
	XC	6,064,783	05/16/00	Congdon et al.			
	XD	5,772,758	06/30/98	Collins et al.			
	XE	5,666,376	09/09/97	Cheng			
	XF	5,976,953	11/02/99	Zavracky et al.			
	XG	5,578,162	11/26/96	D'Asaro et al.			
	XH	5,585,167	12/17/96	Satoh et al.			
	XI	5,674,813	10/07/97	Nakamura et al.			
	XJ	5,574,296	11/12/96	Park et al.			
	XK	6,504,189	01/07/03	Matsuda et al.			
	XL	5,987,196	11/16/99	Noble			
	XM						
	XN						
	XO						
	XP						
	XQ						
	XR						
	XS						
	XT						
	XU						
	XV						
	XW						
	XX						
	XY						
	XZ						
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	CBC	EP 1 035 759	09/13/00	Europe	
	CBD	EP 0 860 913	08/26/95	EUROPE	
	CBE	5-232307	09/10/93	JAPAN W/ENGLISH ABSTRACT	
	CBF	5-243525	09/31/93	JAPAN W/ENGLISH ABSTRACT	
	CBG	3-171617	07/25/91	JAPAN W/ENGLISH ABSTRACT	
	CBH	EP 1 089 338	04/04/01	EUROPE	
	CBI	01 294594	11/28/99	JAPAN (ABSTRACT)	
	CBJ	05 221800	08/31/93	JAPAN (ABSTRACT)	
	CBK	03-149882	11/07/89	JAPAN	
	CBL	0 614 256	09/07/94	EUROPE	
	CBM	1 054 442	11/22/00	EUROPE	
	CBN	0 852 416	07/08/98	EUROPE	
	CBO	W0 02/08806	01/31/02	WIPO	
	CBP	W0 01/59837	08/16/01	WIPO	
	CBQ	62-245205	10/26/87	JAPAN W/ENGLISH ABSTRACT	
	CBR	0 600 658	06/08/94	EUROPE	
	CBS	0 412 002	02/06/91	EUROPE	
	CBT	2000-349278	12/15/00	JAPAN (ENGLISH ABSTRACT)	
	CBU	01-196809	08/08/89	JAPAN (ENGLISH ABSTRACT)	
	CBV	0 619 283	10/12/94	EUROPE	
	CBW	0 661 561	07/05/95	EUROPE	
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	KKAO	Charles Kittel: "Introduction to Solid State Physics"; John Wiley & Sons, Inc. Fifth Edition; pp. 415		
	KKAP	Chyuan-Wei Chen et al: "Liquid-phase epitaxial growth and characterization of InGaAsP layers grown on GaAsP substrates for application to orange light-emitting diodes"; 931 Journal of Applied Physics; 77 (1995) 15 January, No. 2; Woodbury, NY, US; pp. 905-909		
	KKAQ	W. Zhu et al.: "Oriented diamond films grown on nickel substrates"; 320 Applied Physics Letters; 63(1993) September, No. 12, Woodbury, NY, US; pp. 1640-1642		
	KKAR	M. Schreck et al.; "Diamond/Ir/SrTiO <sub>3</sub> : A material combination for improved heteroepitaxial diamond films"; Applied Physics Letters; Vol. 74, No. 5; February 1, 1999; pp. 650-652		
	KKAS	Yoshihiro Yokota et al.; "Cathodoluminescence of boron-doped heteroepitaxial diamond films on platinum"; Diamond and Related Materials 8(1999); pp. 1587-1591		
	KKAT	J.R. Busch et al.; "LINEAR ELECTRO-OPTIC RESPONSE IN SOL-GEL PZT PLANAR WAVEGUIDE"; Electronics Letters; 13th August 1992; Vol. 28, No. 17; pp. 1591-1592		
	KKAU	R. Droopad et al; "Epitaxial Oxide Films on Silicon: Growth, Modeling and Device Properties"; Mat. Res. Soc. Symp. Proc. Vol. 619; 2000 Materials Research Society; pp. 155-165		
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	KKAW	Lin Li; "Ferroelectric/Superconductor Heterostructures"; Materials Science and Engineering; 29 (2000) pp. 153-181		
	KKAX	L. Fan et al.; "Dynamic Beam Switching of Vertical-Cavity Surface-Emitting Lasers with Integrated Optical Beam Routers"; IEEE Photonics Technology Letters; Vol. 9, No. 4; April 4, 1997; pp. 505-507		
	KKAY	Y. Q. Xu. et al.; "(Mn, Sb) doped-Pb(Zr,Ti)O <sub>3</sub> infrared detector arrays"; Journal of Applied Physics; Vol. 88, No. 2; 15 July 2000; pp. 1004-1007		
	KKAZ	Kiyoko Kato et al.; "Reduction of dislocations in InGaAs layer on GaAs using epitaxial lateral overgrowth"; 2300 Journal of Crystal Growth 115 (1991) pp. 174-179; December 1991		
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	LLAB			
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	LLAE			
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	XN	6,233,435 B1	05/15/01	WONG			
	XO	4,723,321	02/02/88	SALEH			
	XP	6,181,920 B1	01/30/01	DENT ET AL			
	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
	XR	5,760,740	06/02/98	BLODGETT			
	XS	5,238,877	08/24/93	RUSSELL			
	XT	4,876,218	10/24/89	PESSA ET AL			
	XU	6,232,242 B1	05/15/01	HATA ET AL			
	XV	4,378,259	03/29/83	HASEGAWA ET AL			
	XW	6,278,541 B1	08/21/01	BAKER			
	XY	4,298,247	11/03/81	MICHELET ET AL			
	XZ	4,174,504	11/13/79	CHENAUSKY ET AL			
	YA	3,758,199	09/11/73	THAXTER			
	YB	6,362,558 B1	03/26/02	FUKUI			
	YC	6,140,746	10/31/00	MIYASHITA ET AL			
	YD	2002/0076878 A1	06/20/02	WASA ET AL			
	YE	6,419,849 B1	07/16/02	QIU ET AL			
	YF	2002/0179000 A1	12/05/02	LEE ET AL			
	YG	6,341,851	01/29/02	TAKAYAMA ET AL			
	YH	2001/0055820 A1	12/27/01	SAKURAI ET AL			
	YI	6,204,525 B1	03/20/01	SAKURAI ET AL			
	YJ	5,985,404	11/16/99	YANO ET AL			
	YK	6,538,359 B1	03/25/03	HIRAKU ET AL			
	YL	6,498,358 B1	12/24/02	LACH ET AL			
	YM	5,387,811	02/07/95	SAIGOH			
	YN	5,523,602	06/04/96	HORIUCHI ET AL			
	YO	5,362,998	11/08/94	IWAMURA ET AL			
	YP	5,188,976	02/23/93	KUME ET AL			
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	YQ	6,501,121 B1	12/31/02	YU ET AL			
	YR	5,919,515	07/06/99	YANO ET AL			
	YS	5,238,877	08/24/93	RUSSELL			
	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
	YY	2002/0021855	02/21/02	KIM			
	YZ	6,110,840	08/29/00	YU			
	ZA	5,667,586	09/16/97	EK ET AL			
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
	ZC	5,315,128	05/24/94	HUNT ET AL			
	ZD	5,919,522	07/06/99	BAUM ET AL			
	ZE	4,843,609	06/27/89	OHYA ET AL			
	ZF	4,626,878	12/02/86	KUWANO ET AL			
	ZG	4,525,871	06/25/85	FOYT ET AL			
	ZH	3,818,451	06/18/74	COLEMAN			
	ZI	6,059,895	05/09/00	CHU ET AL			
	ZJ	4,447,116	05/08/84	KING ET AL			
	ZK	6,022,671	02/08/00	BINKLEY ET AL			
	ZL	5,754,714	05/19/98	SUZUKI ET AL			
	ZM	6,524,651 B2	02/25/03	GAN ET AL			
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL			
	ZO	5,642,371	06/24/97	TOHYAMA ET AL			
	ZP	6,445,724 B2	09/03/02	ABELES			
	ZQ	5,753,934	05/19/98	YANO ET AL			
	ZR	6,326,667 B1	12/04/01	SUGIYAMA ET AL			
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	CDA					
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	CDD					
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	LLAE	Jong-Gul YOON; "Growth of Ferroelectric LiNbO <sub>3</sub> Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651		
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CCT		WO 95/02904	01/26/95	WIPO			
CCU		WO 02/009150	01/31/02	WIPO			
CCV		0 766 292	04/02/97	EUROPE			
CCW		198 29 609	01/05/00	GERMANY			
CCX		1 069 605	01/17/01	EUROPE			
CCY		0 828 287	03/11/98	EUROPE			
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